The RF Line **UHF Power Transistor**

... designed primarily for large-signal output and driver amplifier stages to 1.0 GHz.

- Designed for Class A Linear Power Amplifiers
- Specified 25 Volt, 900 MHz Characteristics: Output Power - 6.0 Watts Power Gain - 6.5 dB Min, Class AB
- Gold Metallization for Improved Reliability

CASE 244-04, STYLE 1 (.280 SOE)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	30	Vdc
Collector-Base Voltage	VCBO	60	Vdc
Emitter–Base Voltage	VEBO	4.0	Vdc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	50 0.286	Watts W/°C
Operating Junction Temperature	ТJ	200	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

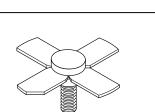
THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction to Case (T _C = 70°C)	R _θ JC	3.5	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = 20 \text{ mA}, I_B = 0$)	V(BR)CEO	30	-	-	Vdc
Collector–Emitter Breakdown Voltage $(I_{C} = 20 \text{ mA}, V_{BE} = 0)$	V _(BR) CES	60	-	-	Vdc
Collector–Base Breakdown Voltage ($I_C = 20 \text{ mA}, I_E = 0$)	V _(BR) CBO	60	-	-	Vdc
Emitter–Base Breakdown Voltage $(I_E = 5.0 \text{ mA}, I_C = 0)$	V _{(BR)EBO}	4.0	-	_	Vdc
Collector Cutoff Current ($V_{CB} = 25 \text{ V}, I_E = 0$)	ICBO	_	-	3.0	mAdc
ON CHARACTERISTICS					
DC Current Gain (I _C = 1.0 mA, V_{CE} = 5.0 V)	hFE	20	-	80	—
DYNAMIC CHARACTERISTICS					
Output Capacitance (V_{CB} = 28 V, I _E = 0, f = 1.0 MHz)	C _{ob}	_	-	19.5	pF
FUNCTIONAL TESTS					-
Common Emitter Amplifier Power Gain ($V_{CE} = 25 \text{ V}, \text{ P}_{Out} = 6.0 \text{ W}, \text{ f} = 900 \text{ MHz}, \text{ I}_{C} = 0.85 \text{ A}$)	GPE	6.5	7.5	-	dB
Load Mismatch (V _{CE} = 25 V, P _{OUt} = 6.0 W, f = 900 MHz, Load VSWR = ∞ :1, All Phase Angles)	Ψ	No Degradation in Output Power			





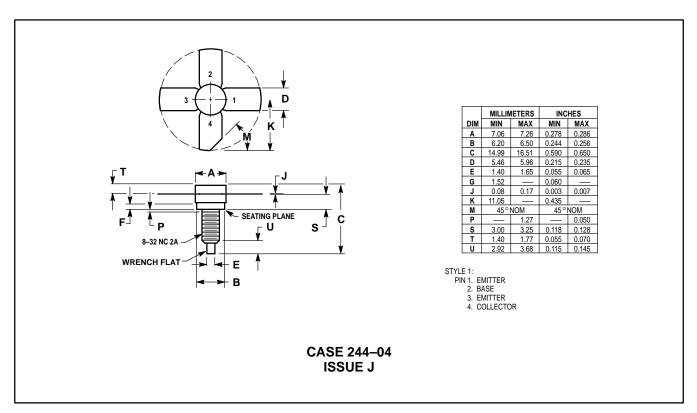
MRF1032

6.0 W, TO 1.0 GHz LINEAR

UHF POWER TRANSISTOR NPN SILICON



PACKAGE DIMENSIONS



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